

今回原理試作挑戦に使うのはP型の高抵抗シリコンWaferです。

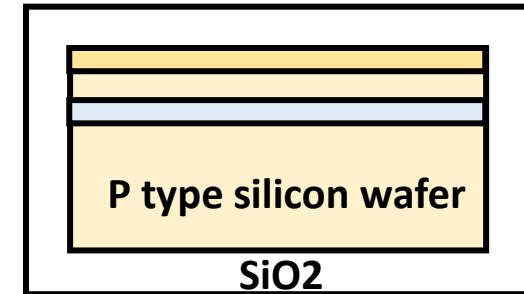
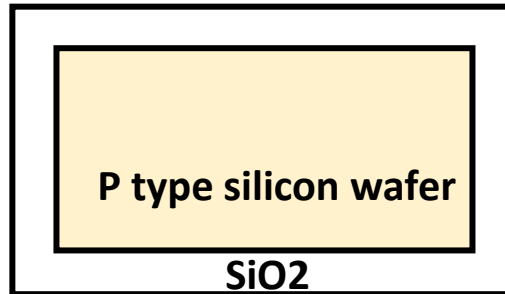
$$\rho = 100 \, \Omega\text{cm} \sim DP = 10E14\text{cm}^{-3};$$

(A)

(B)

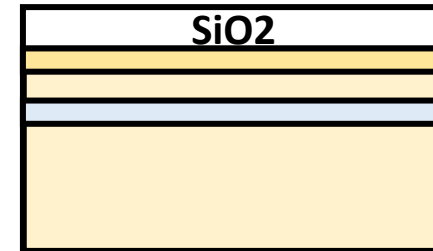
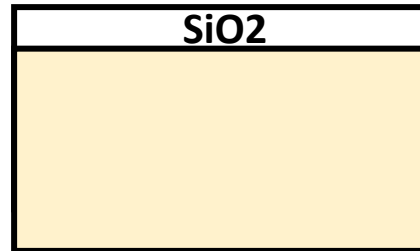
Step 1

全面酸化



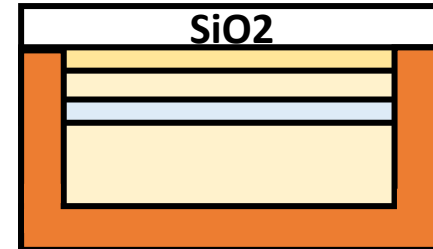
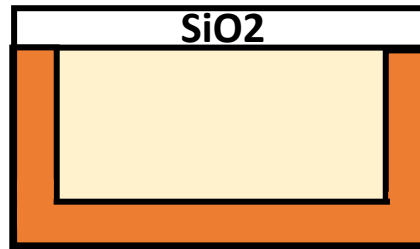
Step 2

裏面と側面の
酸化膜除去



Step 3

裏面と側面に
P+領域の形成

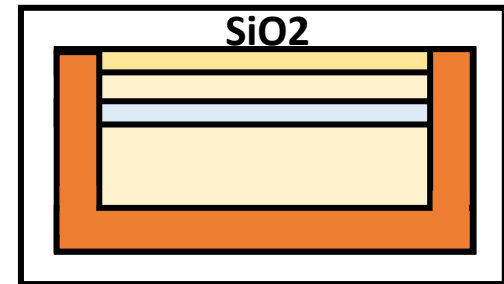
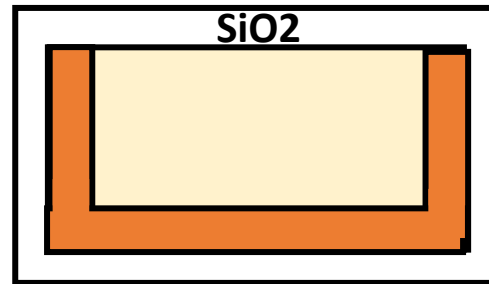


(A)

(B)

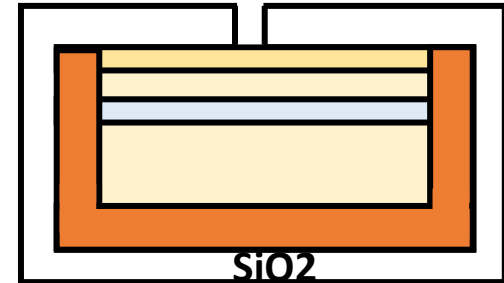
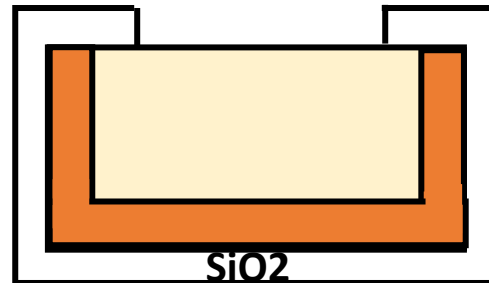
Step 4

第 2 全面酸化



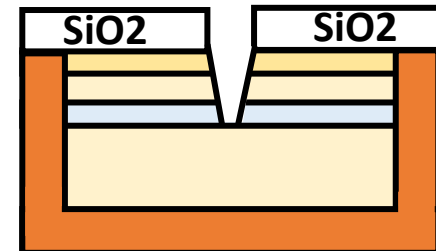
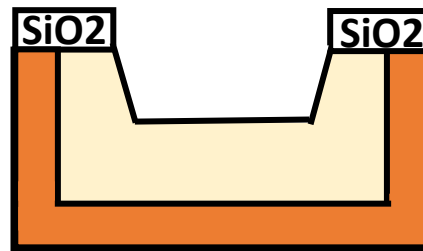
Step 5 MASK01

N+ 領域の
酸化膜の窓開け



Step 6

KOH液による
Silicon Etching

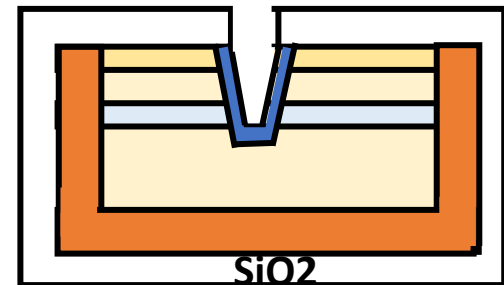
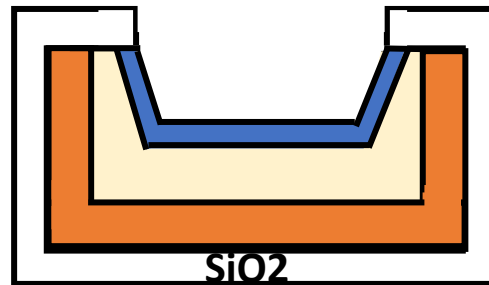


(A)

(B)

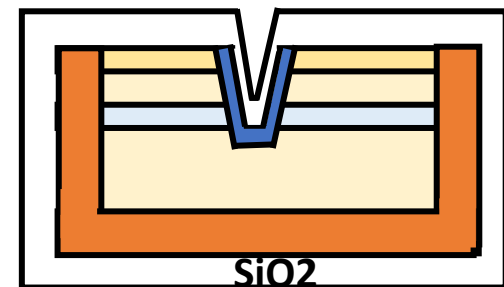
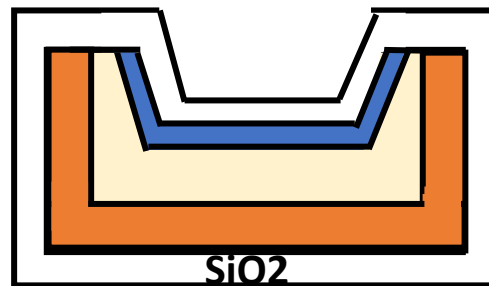
Step 7

N+領域の形成



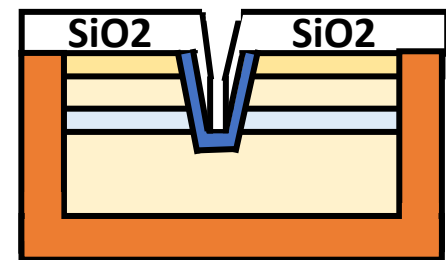
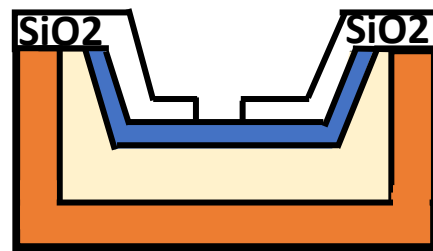
Step 8

第3全面酸化



Step 9 MASK02

金属配線用
窓開け

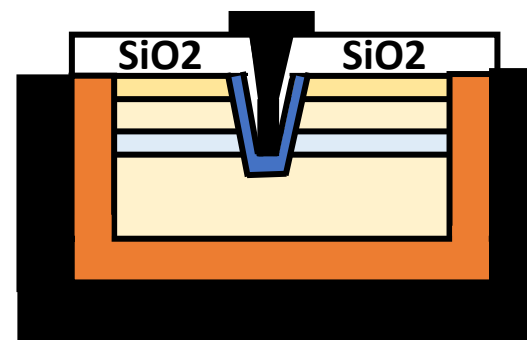
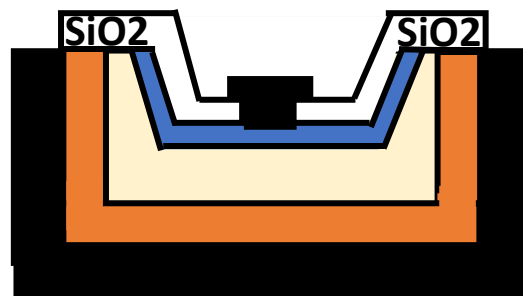


(A)

(B)

Step 10 MASK03

金属配線



完成図

(A)

(B)

